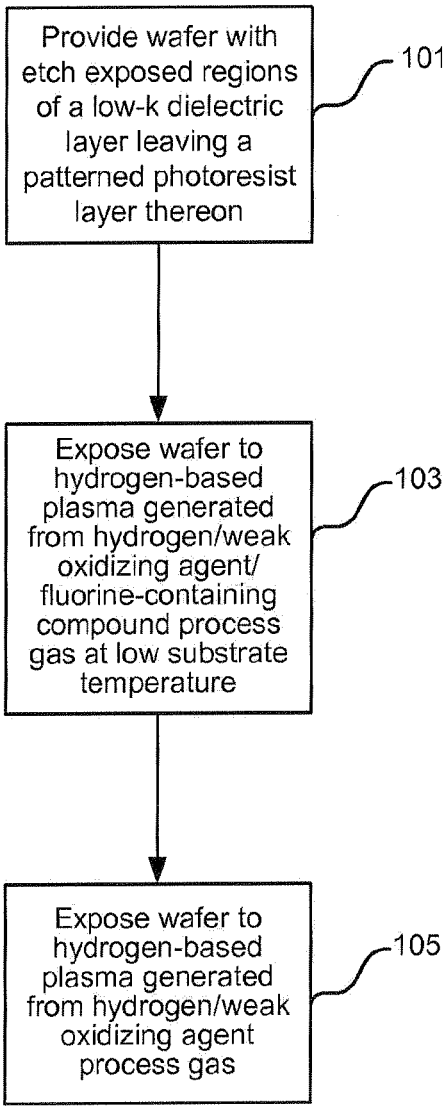

Provide wafer with etch exposed regions of a low-k dielectric layer leaving a patterned photoresist layer thereon
101
Expose wafer to hydrogen-based plasma generated from hydrogen/weak oxidizing agent/ fluorine-containing compound process gas at low substrate temperature
103
Expose wafer to hydrogen-based plasma generated from hydrogen/weak oxidizing agent process gas
105

FIGURE 1

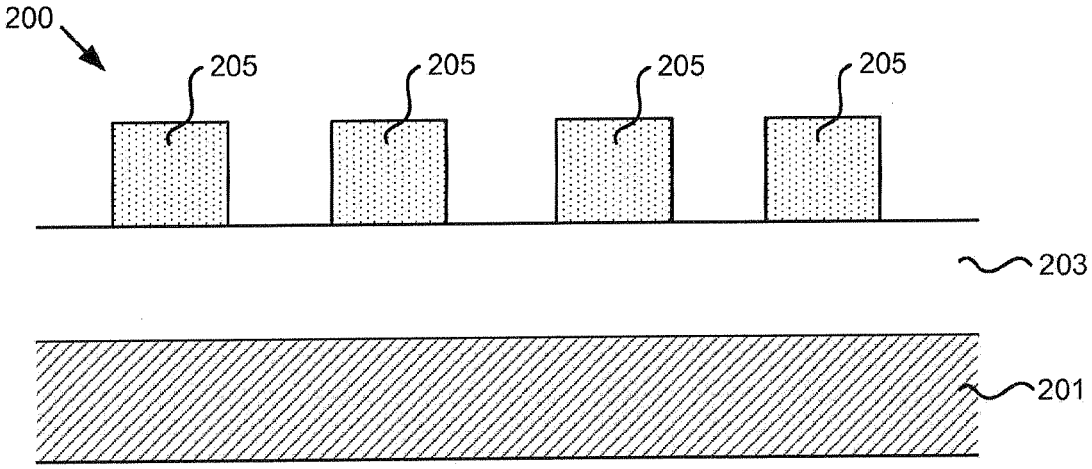


FIGURE 2A

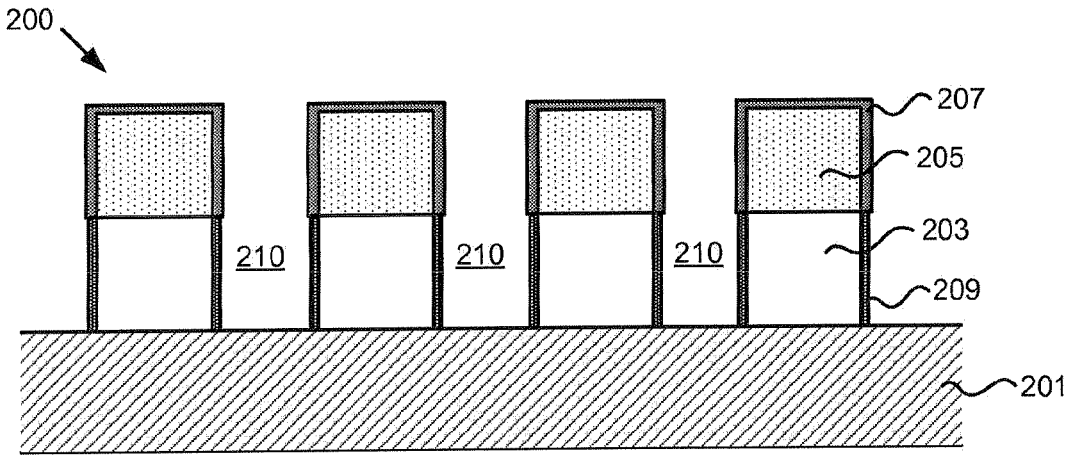


FIGURE 2B

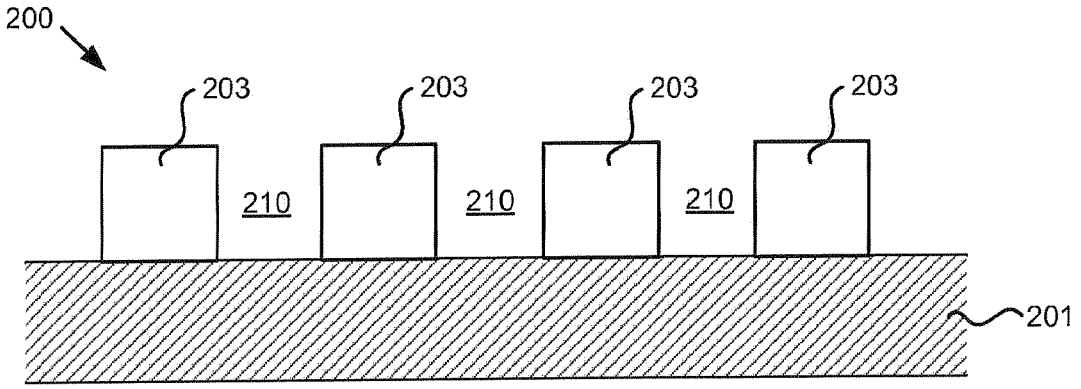


FIGURE 2C

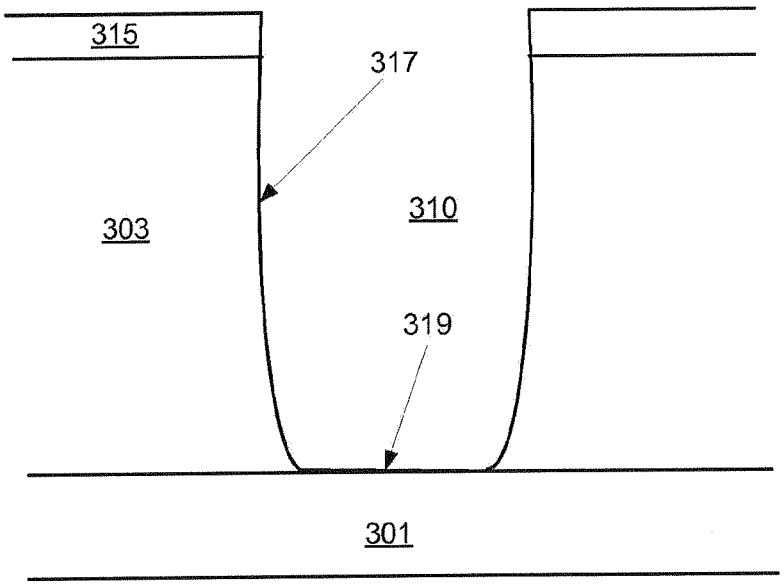


FIGURE 3A

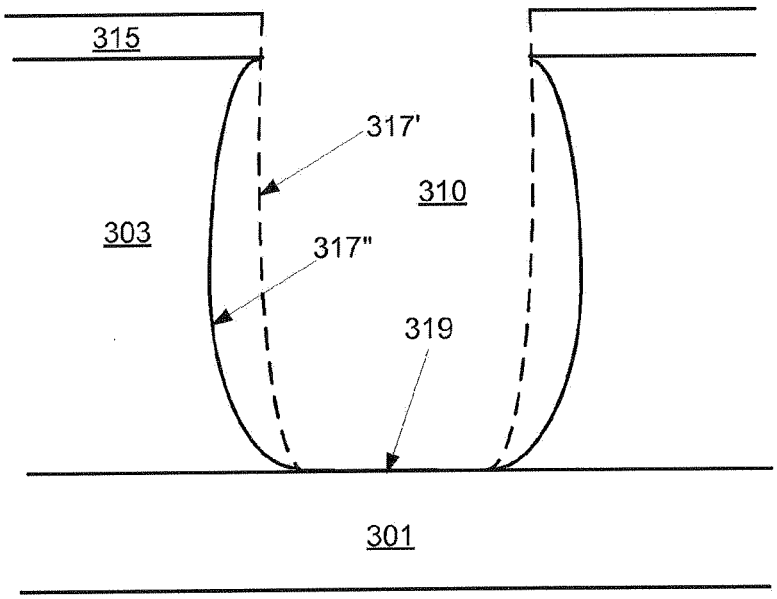


FIGURE 3B

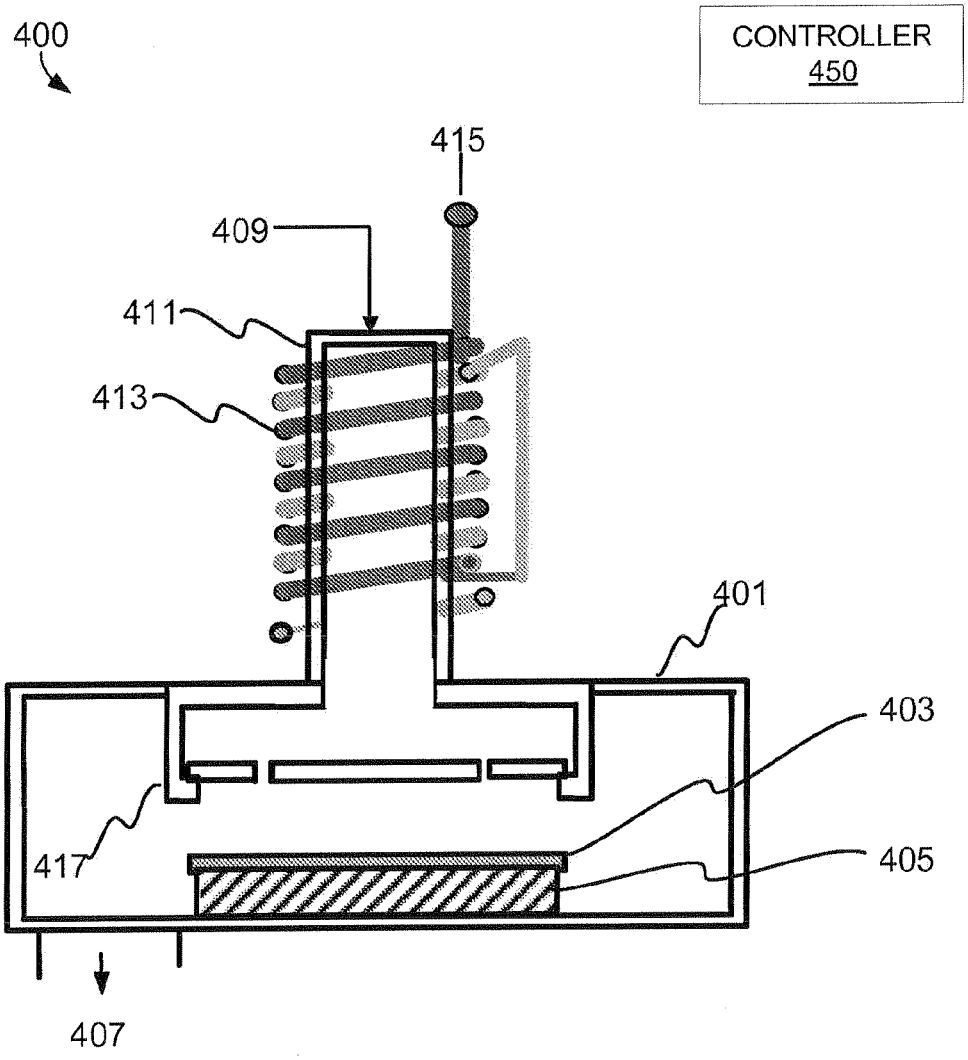


FIGURE 4A

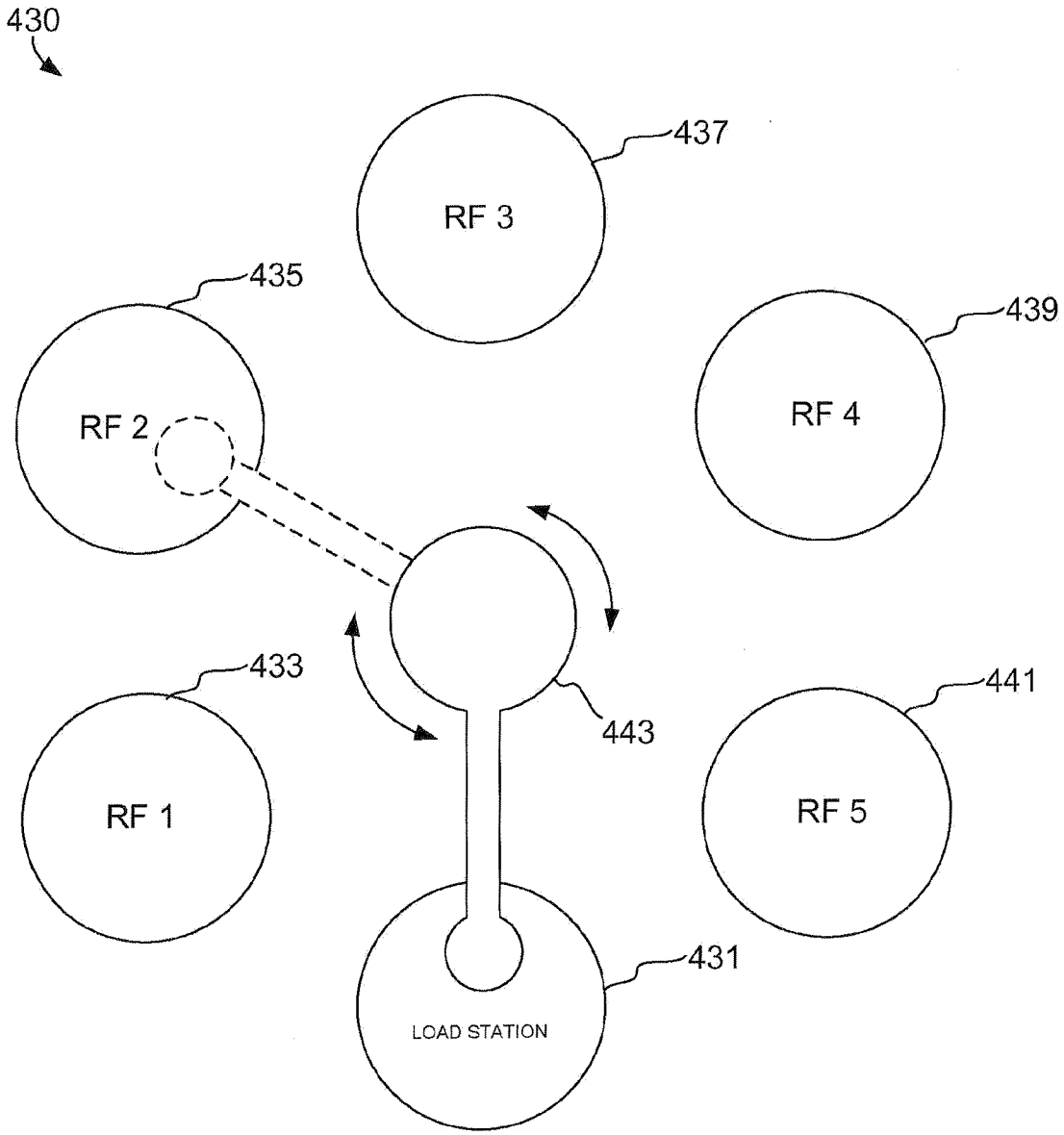

430
437
RF 3
435
439
RF 2
RF 4
433
441
443
RF 1
RF 5
431
LOAD STATION

FIGURE 4B